

Ikuo Suemune

List of Publications by Year in descending order

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5,561
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101543

36
h-index

128289

60
g-index

327
all docs

327
docs citations

327
times ranked

2766
citing authors

#	ARTICLE	IF	CITATIONS
1	Reexamination of N composition dependence of coherently grown GaNAs band gap energy with high-resolution x-ray diffraction mapping measurements. Applied Physics Letters, 1999, 74, 1254-1256.	3.3	244
2	Extremely wide modulation bandwidth in a low threshold current strained quantum well laser. Applied Physics Letters, 1988, 53, 1378-1380.	3.3	222
3	Comment on Polarization Dependent Momentum Matrix Elements in Quantum Well Lasers. Japanese Journal of Applied Physics, 1984, 23, L35-L36.	1.5	196
4	Growth and characterization of hypothetical zinc-blende ZnO films on GaAs(001) substrates with ZnS buffer layers. Applied Physics Letters, 2000, 76, 550-552.	3.3	188
5	Luminescent porous silicon synthesized by visible light irradiation. Applied Physics Letters, 1993, 62, 1429-1431.	3.3	127
6	Band-mixing effects and excitonic optical properties in GaAs quantum wire structures-comparison with the quantum wells. IEEE Journal of Quantum Electronics, 1988, 24, 1778-1790.	1.9	126
7	Role of nitrogen in the reduced temperature dependence of band-gap energy in GaNAs. Applied Physics Letters, 2000, 77, 3021-3023.	3.3	118
8	Nitrogen-Doped p-Type ZnO Layers Prepared with H ₂ O Vapor-Assisted Metalorganic Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 2002, 41, L1281-L1284.	1.5	118
9	Symmetric quantum dots as efficient sources of highly entangled photons: Violation of Bell's inequality without spectral and temporal filtering. Physical Review B, 2013, 88, .	3.2	116
10	Temperature dependence of band gap energies of GaAsN alloys. Applied Physics Letters, 2000, 76, 1285-1287.	3.3	107
11	Corrections to the expression for gain in GaAs. IEEE Journal of Quantum Electronics, 1990, 26, 213-216.	1.9	103
12	Self-Ordering of Nanofacets on Vicinal SiC Surfaces. Physical Review Letters, 2003, 91, 226107.	7.8	89
13	Quantum Mechanical Size Effect Modulation Light Sources – A New Field Effect Semiconductor Laser or Light Emitting Device. Japanese Journal of Applied Physics, 1983, 22, L22-L24.	1.5	78
14	Theoretical study of differential gain in strained quantum well structures. IEEE Journal of Quantum Electronics, 1991, 27, 1149-1159.	1.9	71
15	Field effects on the refractive index and absorption coefficient in AlGaAs quantum well structures and their feasibility for electrooptic device applications. IEEE Journal of Quantum Electronics, 1987, 23, 2167-2180.	1.9	66
16	Controllable enhancement of excitonic spontaneous emission by quantum confined Stark effect in GaAs quantum wells embedded in quantum microcavities. Applied Physics Letters, 1991, 58, 2735-2737.	3.3	60
17	Analysis of temperature dependent optical gain of strained quantum well taking account of carriers in the SCH layer. IEEE Photonics Technology Letters, 1994, 6, 344-347.	2.5	55
18	Bandgap Energy of GaNAs Alloys Grown on (001) GaAs by Metalorganic Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1997, 36, L1572-L1575.	1.5	55

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19	Position controlled nanowires for infrared single photon emission. Applied Physics Letters, 2010, 97, .	3.3	55
20	Study of Luminescent Region in Anodized Porous Silicons by Photoluminescence Imaging and Their Microstructures. Japanese Journal of Applied Physics, 1992, 31, L490-L493.	1.5	53
21	Extremely low threshold and high temperature operation in a photopumped ZnSe/ZnSSe blue laser. Applied Physics Letters, 1991, 59, 1401-1403.	3.3	51
22	Incidence angle effect of a hydrogen plasma beam for the cleaning of semiconductor surfaces. Applied Physics Letters, 1989, 55, 760-762.	3.3	48
23	Photoirradiation Effect on Photoluminescence from Anodized Porous Silicons and Luminescence Mechanism. Japanese Journal of Applied Physics, 1992, 31, L494-L497.	1.5	46
24	Nucleation and growth kinetics of AlN films on atomically smooth 6H-SiC (0001) surfaces. Applied Physics Letters, 2001, 78, 3612-3614.	3.3	46
25	Blue light stimulated emission from a localized state formed by well barrier fluctuation in a III-V semiconductor superlattice. Applied Physics Letters, 1992, 61, 1182-1184.	3.3	45
26	Epitaxial growth of zincblende ZnSe/MgS superlattices on (001) GaAs. Applied Physics Letters, 1996, 68, 844-846.	3.3	44
27	Growth and luminescence properties of self-organized ZnSe quantum dots. Applied Physics Letters, 1999, 75, 235-237.	3.3	44
28	Luminescence properties of ZnO films grown on GaAs substrates by molecular-beam epitaxy excited by electron cyclotron resonance oxygen plasma. Journal of Crystal Growth, 2000, 214-215, 280-283.	1.5	44
29	Role of ZnS buffer layers in growth of zincblende ZnO on GaAs substrates by metalorganic molecular-beam epitaxy. Journal of Crystal Growth, 2000, 221, 435-439.	1.5	42
30	Luminescence of a Cooper Pair. Physical Review Letters, 2009, 103, 187001.	7.8	41
31	Vanishing fine-structure splittings in telecommunication-wavelength quantum dots grown on (111)A surfaces by droplet epitaxy. Physical Review B, 2014, 90, .	3.2	41
32	Lasing in a ZnS _{0.12} Se _{0.88} /ZnSe multilayer structure with photopumping. Applied Physics Letters, 1989, 54, 981-983.	3.3	40
33	Effect of indium doping on the transient optical properties of GaN films. Applied Physics Letters, 1999, 75, 2879-2881.	3.3	40
34	Superconductor-Based Quantum-Dot Light-Emitting Diodes: Role of Cooper Pairs in Generating Entangled Photon Pairs. Japanese Journal of Applied Physics, 2006, 45, 9264-9271.	1.5	38
35	Field-induced modulations of refractive index and absorption coefficient in a GaAs/AlGaAs quantum well structure. Electronics Letters, 1986, 22, 888.	1.0	37
36	Temperature dependent carrier dynamics in telecommunication band InAs quantum dots and dashes grown on InP substrates. Journal of Applied Physics, 2013, 113, .	2.5	37

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37	New low-temperature process for growth of GaAs on Si with metalorganic molecular beam epitaxy assisted by a hydrogen plasma. Applied Physics Letters, 1988, 53, 2173-2175.	3.3	36
38	Characterization of Nitrogen-Doped ZnSe and ZnS _{0.06} Se _{0.94} Films Grown by Metal-Organic Vapor-Phase Epitaxy. Japanese Journal of Applied Physics, 1988, 27, L2195-L2198.	1.5	36
39	Mass Spectrometric Study and Modeling of Decomposition Process of Tris-Dimethylamino-Arsenic on (001) GaAs Surface. Japanese Journal of Applied Physics, 1991, 30, L1579-L1582.	1.5	36
40	Photoluminescence study of InAs quantum dots embedded in GaNAs strain compensating layer grown by metalorganic-molecular-beam epitaxy. Journal of Applied Physics, 2002, 92, 6813-6818.	2.5	36
41	Growth and structural characterization of III-V semiconductor alloys. Semiconductor Science and Technology, 2002, 17, 755-761.	2.0	36
42	Deterministic Single-Photon and Polarization-Correlated Photon Pair Generations From a Single InAlAs Quantum Dot. Journal of Nanoelectronics and Optoelectronics, 2006, 1, 39-51.	0.5	35
43	In-Situ RHEED Monitoring of Hydrogen Plasma Cleaning on Semiconductor Surfaces. Japanese Journal of Applied Physics, 1990, 29, 2273-2276.	1.5	33
44	Stability of CdSe and ZnSe dots self-organized on semiconductor surfaces. Applied Physics Letters, 1997, 71, 3886-3888.	3.3	33
45	Metalorganic molecular beam epitaxy of GaNAs alloys on (001)GaAs. Journal of Crystal Growth, 1998, 189-190, 490-495.	1.5	33
46	Surface-emitting stimulated emission in high-quality ZnO thin films. Journal of Applied Physics, 2004, 96, 3733-3736.	2.5	32
47	Enhanced Photon Generation in a Nb Light Emitting Device. Physical Review Letters, 2011, 107, 157403.	1.5	32
48	Low-temperature GaAs epitaxial growth using electron-cyclotron resonance/metalorganic-molecular-beam epitaxy. Journal of Applied Physics, 1988, 64, 2778-2780.	2.5	31
49	High Output Power (>20 W) and High Quantum Efficiency in a Photopumped ZnSe/ZnS _{Se} Blue Laser Operating at Room Temperature. Japanese Journal of Applied Physics, 1991, 30, L1399-L1401.	1.5	31
50	Superconductor-based Light Emitting Diode: Demonstration of Role of Cooper Pairs in Radiative Recombination Processes. Applied Physics Express, 2008, 1, 011701.	2.4	29
51	Single-photon emission in telecommunication band from an InAs quantum dot grown on InP with molecular-beam epitaxy. Applied Physics Letters, 2013, 103, .	3.3	29
52	Improvement of InAs quantum-dot optical properties by strain compensation with GaNAs capping layers. Applied Physics Letters, 2003, 83, 4524-4526.	3.3	28
53	Noncontact photoacoustic measurements of semiconductors with Michelson interferometry. Journal of Applied Physics, 1985, 58, 615-617.	2.5	27
54	Electroreflectance Spectra and Field-Induced Variation in Refractive Index of a GaAs/AlAs Quantum Well Structure at Room Temperature. Japanese Journal of Applied Physics, 1986, 25, L640-L642.	1.5	27

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55	Atomic layer epitaxy of GaAs and role of As-source materials on self-limiting mechanism. Applied Physics Letters, 1992, 60, 1498-1500.	3.3	27
56	Single-crystalline rocksalt CdO layers grown on GaAs (001) substrates by metalorganic molecular-beam epitaxy. Applied Physics Letters, 2001, 79, 470-472.	3.3	27
57	Microcavities with distributed Bragg reflectors based on ZnSe/MgS superlattice grown by MOVPE. Journal of Crystal Growth, 2000, 221, 699-703.	1.5	26
58	Transient Response of Photoluminescence for Electric Field in a GaAs/Al _{0.7} Ga _{0.3} As Single Quantum Well: Evidence for Field-Induced Increase in Carrier Life Time. Japanese Journal of Applied Physics, 1985, 24, L586-L588.	1.5	25
59	GaNAs as Strain Compensating Layer for 1.55 μ m Light Emission from InAs Quantum Dots. Japanese Journal of Applied Physics, 2003, 42, 5598-5601.	1.5	24
60	Epitaxial ZnO growth and p-type doping with MOMBE. Physica Status Solidi (B): Basic Research, 2004, 241, 640-647.	1.5	24
61	Photon Antibunching Observed from an InAlAs Single Quantum Dot. Japanese Journal of Applied Physics, 2005, 44, L793-L796.	1.5	24
62	Near-Room-Temperature Photopumped Blue Lasers in Zn _{Sx} Se _{1-x} /ZnSe Multilayer Structures. Japanese Journal of Applied Physics, 1990, 29, L2420-L2422.	1.5	23
63	X-ray photoelectron spectroscopy and atomic force microscopy surface study of GaAs(100) cleaning procedures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 77.	1.6	23
64	Self-Organized CdSe Quantum Dots on (100)ZnSe/GaAs Surfaces Grown by Metalorganic Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1997, 36, 4097-4101.	1.5	23
65	H ₂ O-Vapor-Activated ZnO Growth on a-Face Sapphire Substrates by Metalorganic Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 2002, 41, 2851-2854.	1.5	23
66	Photon-spin qubit-conversion based on Overhauser shift of Zeeman energies in quantum dots. Applied Physics Letters, 2005, 87, 112506.	3.3	23
67	Gain-switching characteristics and fast transient response of three-terminal size-effect modulation laser. IEEE Journal of Quantum Electronics, 1986, 22, 1900-1908.	1.9	22
68	Selective formation of luminescent porous silicon by photosynthesis. Journal of Applied Physics, 1994, 75, 4765-4767.	2.5	22
69	Semiconductor photonic dots: Visible wavelength-sized optical resonators. Applied Physics Letters, 1999, 74, 1963-1965.	3.3	22
70	Strain effect on the N composition dependence of GaNAs bandgap energy grown on (001) GaAs by metalorganic molecular beam epitaxy. Journal of Crystal Growth, 1999, 201-202, 355-358.	1.5	22
71	Theory of strain states in InAs quantum dots and dependence on their capping layers. Journal of Applied Physics, 2005, 98, 063502.	2.5	22
72	A Cooper-Pair Light-Emitting Diode: Temperature Dependence of Both Quantum Efficiency and Radiative Recombination Lifetime. Applied Physics Express, 2010, 3, 054001.	2.4	21

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73	Optical and structural characterizations of ZnSe/ZnSSe superlattices grown by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , 1992, 72, 3029-3033.	2.5	20
74	Highly conductive GaAsNSe alloys grown on GaAs and their nonalloyed ohmic properties. <i>Applied Physics Letters</i> , 2001, 79, 3284-3286.	3.3	20
75	Bright single-photon source based on an InAs quantum dot in a silver-embedded nanocone structure. <i>Applied Physics Letters</i> , 2013, 102, 131114.	3.3	20
76	Switching of photoluminescence by pulsed electric field in GaAs/Al _{0.7} Ga _{0.3} As single quantum well structure. <i>IEEE Journal of Quantum Electronics</i> , 1986, 22, 1837-1844.	1.9	19
77	Lattice-Mismatch Enhanced Diffusion at a ZnSe/GaAs Interface - Increase of Thermal Stability in a Lattice-Matching System. <i>Japanese Journal of Applied Physics</i> , 1987, 26, L2072-L2075.	1.5	19
78	Optical properties of highly excited ZnSe/ZnSxSe1-x multiple-quantum-well structures. <i>Semiconductor Science and Technology</i> , 1992, 7, 681-685.	2.0	19
79	Anomalous dip observed in intensity autocorrelation function as an inherent nature of single-photon emitters. <i>Applied Physics Letters</i> , 2012, 101, .	3.3	19
80	Stable and efficient collection of single photons emitted from a semiconductor quantum dot into a single-mode optical fiber. <i>Applied Physics Express</i> , 2016, 9, 032801.	2.4	19
81	Excitonic properties of zinc-blende ZnSe/MgS superlattices studied by reflection spectroscopy. <i>Physical Review B</i> , 1997, 55, 4449-4455.	3.2	18
82	GaN Quantum Structures with Fractional Dimension " From Quantum Well to Quantum Dot. <i>Physica Status Solidi (B): Basic Research</i> , 1999, 216, 431-434.	1.5	18
83	Control of ZnSe Film Stoichiometry at ZnSe/GaAs Interface Grown by MOCVD. <i>Japanese Journal of Applied Physics</i> , 1986, 25, L827-L829.	1.5	17
84	Observation of optical bistability by charge-induced self-feedback in biased AlGaAs multiple quantum well structures. <i>Applied Physics Letters</i> , 1990, 57, 419-421.	3.3	17
85	Atomic layer epitaxy of AlAs using trimethylamine-alane and aminoAs. <i>Applied Physics Letters</i> , 1993, 62, 1420-1422.	3.3	17
86	Excitonic luminescence up to room temperature in a ZnSe/MgS superlattice. <i>Applied Physics Letters</i> , 1997, 70, 2350-2352.	3.3	17
87	Electron effective mass and mobility in heavily doped n-GaN probed by Raman scattering. <i>Journal of Applied Physics</i> , 2008, 103, 103528.	2.5	17
88	Band-edge hole mass in strained-quantum-well structures. <i>Physical Review B</i> , 1991, 43, 14099-14106.	3.2	16
89	Excitonic properties of ZnSe/ZnSeS superlattices. <i>Applied Physics Letters</i> , 1994, 64, 2439-2441.	3.3	16
90	Atomic force microscope lithography on carbonaceous films deposited by electron-beam irradiation. <i>Applied Physics Letters</i> , 1998, 72, 716-718.	3.3	16

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91	Study of current-voltage characteristic in a ZnSe-based II-VI laser diode. Applied Physics Letters, 1993, 63, 2612-2614.	3.3	15
92	Large estimated frequency response increase from deep potential well strained quantum well lasers. IEEE Photonics Technology Letters, 1994, 6, 1315-1317.	2.5	15
93	Low-Dimensional II-VI Semiconductor Structures: ZnSe/MgS Superlattices and CdSe Self-Organized Dots. Physica Status Solidi (B): Basic Research, 1997, 202, 845-856.	1.5	15
94	CdO epitaxial layers grown on (001) GaAs surfaces by metalorganic molecular-beam epitaxy. Journal of Crystal Growth, 2002, 237-239, 518-522.	1.5	15
95	Metal-coated semiconductor nanostructures and simulation of photon extraction and coupling to optical fibers for a solid-state single-photon source. Nanotechnology, 2013, 24, 455205.	2.6	15
96	Enhanced Photon Extraction from a Quantum Dot Induced by a Silver Microcolumnar Photon Reflector. Applied Physics Express, 2013, 6, 062801.	2.4	15
97	Fiber-Based Bidirectional Solid-State Single-Photon Emitter Based on Semiconductor Quantum Dot. Applied Physics Express, 2013, 6, 065203.	2.4	15
98	Quantum-confined field-effect light emitters with high-speed switching capability. Applied Physics Letters, 1989, 55, 1149-1151.	3.3	14
99	Room-temperature operation of three-terminal quantum-confined field-effect light emitters. Applied Physics Letters, 1990, 56, 2059-2061.	3.3	14
100	Continuous-Wave Operation of a Lateral Current Injection Ridge Waveguide AlGaAs/GaAs Laser with a Selectively-Doped Heterostructure. Japanese Journal of Applied Physics, 1991, 30, 990-991.	1.5	14
101	Catalytic Precracking of Amino-As in Metalorganic Molecular-Beam Epitaxy of GaAs. Japanese Journal of Applied Physics, 1992, 31, L1272-L1275.	1.5	14
102	Room temperature ultraviolet lasing action in high-quality ZnO thin films. Journal of Luminescence, 2007, 122-123, 828-830.	3.1	14
103	Observation of Acoustic Signals from Semiconductor Lasers. Japanese Journal of Applied Physics, 1981, 20, L9-L12.	1.5	13
104	Quenching of photoluminescence from GaAs/AlGaAs single quantum well by an electric field at high temperature. Superlattices and Microstructures, 1985, 1, 111-113.	3.1	13
105	Electric Field Effect on Subband State Transitions Peaks in the Photoluminescence from a GaAlAs Quantum Well Structure. Japanese Journal of Applied Physics, 1985, 24, L589-L592.	1.5	13
106	Photoacoustic study of surface and bulk nonradiative recombinations in GaAs with two-wavelength excitations. Journal of Applied Physics, 1986, 60, 2621-2623.	2.5	13
107	Thermal stability of nearly lattice-matched ZnSse/GaAs interface grown by MOVPE. Journal of Crystal Growth, 1988, 93, 662-666.	1.5	13
108	Auger effects in acceptor-doped long-wavelength strained quantum well lasers. Applied Physics Letters, 1989, 55, 2579-2581.	3.3	13

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109	Low-Temperature Selective Growth of ZnSe and ZnS on (001) GaAs Patterned with Carbonaceous Mask by Metalorganic Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 1998, 37, L272-L274.	1.5	13
110	Formation of wire-like surfaces and lateral composition modulation in GaAsN grown by metalorganic molecular-beam epitaxy. Journal of Crystal Growth, 2000, 221, 546-550.	1.5	13
111	Structural anisotropy in GaN films grown on vicinal 4H-SiC surfaces by metallorganic molecular-beam epitaxy. Applied Physics Letters, 2003, 83, 1569-1571.	3.3	13
112	Luminescence study on evolution from Te isoelectronic centers to type-II ZnTe quantum dots grown by metalorganic molecular-beam epitaxy. Journal of Crystal Growth, 2007, 301-302, 277-280.	1.5	13
113	Analysis of Intrinsic Saturable Absorption in InGaAs/InP Diode Lasers. Japanese Journal of Applied Physics, 1981, 20, L635-L638.	1.5	12
114	Hole-Burnings Observed at High Energy Tails in Spontaneous Emission Spectra from 1.3 μm -InGaAsP/InP Lasers. Japanese Journal of Applied Physics, 1982, 21, L240-L242.	1.5	12
115	Two-Dimensionally Collimated Output Beam from GaAlAs Diode Lasers with Two-Dimensional Distributed Bragg Reflectors. Japanese Journal of Applied Physics, 1983, 22, L267-L269.	1.5	12
116	Size effect modulation light sources " Possibility of LED mode operation at room temperature. Superlattices and Microstructures, 1985, 1, 335-337.	3.1	12
117	Dynamic Switching Characteristics of Photoluminescence by an Electric Field in AlGaAs Quantum Well Structures. Japanese Journal of Applied Physics, 1987, 26, L1313-L1316.	1.5	12
118	Photopumped lasing in ZnSSe/ZnSe multilayer structures up to 210 K. Journal of Crystal Growth, 1990, 101, 754-757.	1.5	12
119	Desorption properties of amine species during atomic layer epitaxy of GaAs using aminoAs. Applied Physics Letters, 1992, 61, 2577-2579.	3.3	12
120	Photopumped ZnSe/ZnSSe blue semiconductor lasers and a theoretical calculation of the optical gain. Journal of Crystal Growth, 1992, 117, 1068-1072.	1.5	12
121	Atomic Force Microscope Nanolithography on SiO ₂ /Semiconductor Surfaces. Japanese Journal of Applied Physics, 1997, 36, 4057-4060.	1.5	12
122	Atomic force microscope based patterning of carbonaceous masks for selective area growth on semiconductor surfaces. Journal of Applied Physics, 2000, 88, 3158-3165.	2.5	12
123	1.55 μm emission from GalnNAs with indium-induced increase of N concentration. Applied Physics Letters, 2003, 83, 1992-1994.	3.3	12
124	Nucleation Stages of Carbon Nanotubes on SiC(0001) by Surface Decomposition. Japanese Journal of Applied Physics, 2005, 44, L803-L805.	1.5	12
125	Spectral hole burnings at high energy tails in spontaneous emission and hot carrier relaxation in InGaAsP lasers. IEEE Journal of Quantum Electronics, 1983, 19, 924-929.	1.9	11
126	A 140 ps Optical Pulse Generation by Field-Induced Gain Switching in a Photo-Excited Quantum Well Laser. Japanese Journal of Applied Physics, 1987, 26, L117-L119.	1.5	11

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127	Polarization dependent absorption spectra in quantum wire structures. Superlattices and Microstructures, 1988, 4, 19-22.	3.1	11
128	Low-temperature cleaning of Si and growth of GaAs on Si by hydrogen plasma-assisted metalorganic molecular-beam epitaxy. Journal of Crystal Growth, 1989, 95, 91-95.	1.5	11
129	Dependence of GaAs etch rate on the angle of incidence of a hydrogen plasma beam excited by electron cyclotron resonance. Applied Physics Letters, 1990, 56, 2393-2395.	3.3	11
130	Selectively doped double-heterojunction lateral current injection ridge waveguide AlGaAs/GaAs laser. Applied Physics Letters, 1990, 56, 1391-1393.	3.3	11
131	Room-temperature stimulated emission in optically pumped narrow ZnSe/ZnSxSe1-x multiple-quantum-well structures. Journal of Applied Physics, 1992, 72, 4969-4971.	2.5	11
132	Excitonic properties in ZnSe/ZnSxSe1-x strained-layer superlattices by one- and two-photon spectroscopy. Physical Review B, 1994, 49, 14367-14371.	3.2	11
133	X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution. Applied Surface Science, 1994, 82-83, 250-256.	6.1	11
134	Exciton coherence in clean single InP/InAsP/InP nanowire quantum dots emitting in infra-red measured by Fourier spectroscopy. Journal of Physics: Conference Series, 2009, 193, 012132.	0.4	11
135	Analysis of transverse modes of phase-locked multi-stripe lasers. Electronics Letters, 1985, 21, 713.	1.0	10
136	Stability and interdiffusion at MOCVD grown ZnSe/GaAs interfaces. Journal of Crystal Growth, 1988, 86, 467-470.	1.5	10
137	Doping in a superlattice structure: Improved hole activation in wide-gap II-VI materials. Journal of Applied Physics, 1990, 67, 2364-2369.	2.5	10
138	A new optoelectronic device based on modulation-doped heterostructure: demonstration of functions as both lateral current injection laser and junction field effect transistor. IEEE Photonics Technology Letters, 1990, 2, 881-883.	2.5	10
139	Iodine Doping in ZnSe in High-Temperature Range by Metalorganic Vapor-Phase Epitaxy. Japanese Journal of Applied Physics, 1993, 32, L524-L527.	1.5	10
140	MOVPE growth of ZnSe/ZnS distributed Bragg reflectors on GaAs (1 0 0) and (3 1 1)B substrates. Journal of Crystal Growth, 1998, 184-185, 777-782.	1.5	10
141	Nucleation and Faceting in Selectively Grown ZnS Pyramidal Dot Array for Short-Wavelength Light Emitters. Japanese Journal of Applied Physics, 1999, 38, L710-L713.	1.5	10
142	Formation of ohmic contacts top-type ZnO. Physica Status Solidi (B): Basic Research, 2004, 241, 635-639.	1.5	10
143	Transport characteristics of a superconductor-based LED. Superconductor Science and Technology, 2010, 23, 034025.	3.5	10
144	Strongly suppressed multi-photon generation from a single quantum dot in a metal-embedded structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 337-339.	0.8	10

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145	Room-temperature operation of a transverse-distributed-feedback cavity laser. <i>Electronics Letters</i> , 1982, 18, 745.	1.0	9
146	High-Speed Intensity Modulation by Quantum-Confined Field Effect Combined with Modulation of Injection Current in Light-Emitting Triodes. <i>Japanese Journal of Applied Physics</i> , 1990, 29, L967-L970.	1.5	9
147	Theoretical Estimation of Leakage Current in II-VI Heterostructure Lasers. <i>Japanese Journal of Applied Physics</i> , 1992, 31, L95-L98.	1.5	9
148	Pressure-induced conduction-band crossover in a ZnSe/ZnS _{0.18} Se _{0.82} symmetric superlattice. <i>Physical Review B</i> , 1994, 50, 14635-14638.	3.2	9
149	MOVPE growth of ZnSe/ZnMgS distributed Bragg reflectors with high refractive-index contrast. <i>Journal of Crystal Growth</i> , 2000, 214-215, 1019-1023.	1.5	9
150	II-VI quantum dots grown by MOVPE. <i>Journal of Crystal Growth</i> , 2003, 248, 301-309.	1.5	9
151	Intrinsic exciton transitions in high-quality ZnO thin films grown by plasma-enhanced molecular-beam epitaxy on sapphire substrates. <i>Journal of Applied Physics</i> , 2006, 99, 063709.	2.5	9
152	Triggered single-photon emission and cross-correlation properties in InAlAs quantum dot. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 32, 144-147.	2.7	9
153	Superconducting Light-Emitting Diodes. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2015, 21, 1-11.	2.9	9
154	Systematic alterations of excitonic spontaneous emission through continuous uning of emission wavelength in AlGaAs quantum microcavities. <i>Surface Science</i> , 1992, 267, 612-615.	1.9	8
155	High-Resolution Patterning of Luminescent Porous Silicon with Photoirradiation. <i>Japanese Journal of Applied Physics</i> , 1994, 33, 590-593.	1.5	8
156	Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs. <i>Applied Surface Science</i> , 1994, 82-83, 149-157.	6.1	8
157	Temperature Dependence of ZnS Growth with Atmospheric-Pressure Metalorganic Vapor Phase Epitaxy Using Ditertiarybutyl Sulfide. <i>Japanese Journal of Applied Physics</i> , 1995, 34, 4143-4147.	1.5	8
158	Luminescence of Excitons Localized by Monolayer Interface Fluctuations in ZnSe/MgS Superlattices Grown by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1997, 36, 4199-4203.	1.5	8
159	Some effects of conduction band nonparabolicity on electron reflection spectrum of multi-quantum barriers. <i>Journal of Applied Physics</i> , 1998, 84, 4667-4672.	2.5	8
160	Growth mechanism of selectively grown II-VI semiconductor photonic dots for short-wavelength light emitters. <i>Journal of Crystal Growth</i> , 2000, 221, 425-430.	1.5	8
161	Study of Resonance Wavelengths in II-VI Semiconductor Photonic Dots: Pyramidal Size Dependences and Luminescence Properties. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 971-976.	1.5	8
162	The application of an InGaAs ⁺ GaAsN strain-compensated superlattice to InAs quantum dots. <i>Journal of Applied Physics</i> , 2006, 99, 103103.	2.5	8

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